

## Photochromic properties of double layer CdS/MoO<sub>3</sub> thin films

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The sub-stoichiometric molybdenum trioxide (layered  $\alpha$ -MoO<sub>3</sub>) thin films are photochromic and thermochromic and have wide applications in optical data storage and display systems. The optical absorption in these films is caused by the small-polaron hopping between two non-equivalent sites of molybdenum Mo<sup>5+</sup> and Mo<sup>6+</sup>.

The double layer CdS/MoO<sub>3</sub> systems were deposited by sequential evaporation of CdS (thermal evaporation) and MoO<sub>3</sub> (activated reactive evaporation) films on well-cleaned Pyrex glass substrates. The photochromic properties were studied in the spectral range 300 to 1500 nm by illuminating with a 100 W tungsten lamp at various irradiation times. The photochromic behavior was observed of both CdS/MoO<sub>3</sub> and In:CdS/MoO<sub>3</sub> deposited on glass to compare these double layer systems.

The irradiation produced free electrons which are trapped by anion (oxygen) vacancies by forming colour centers. The evaluated maximum colour center concentration was  $1.6 \times 10^{17}/\text{cm}^3$  at a threshold time of 40 minutes. The photochromic behavior and hence the color centre concentration was increased by forming a double layer glass/CdS/MoO<sub>3</sub> system in which CdS and In:CdS were used as interlayer, because of the semiconducting and photosensitive characteristics of CdS. The color center concentration was found to be higher in glass/In:CdS/MoO<sub>3</sub> than the glass/MoO<sub>3</sub> and glass/CdS/MoO<sub>3</sub> systems. The driving force for electron transfer between CdS and MoO<sub>3</sub> is the relative energy difference between the conduction band of the two semiconductors. The conduction band of CdS is more negative than that of MoO<sub>3</sub>. Hence the bottom of the conduction band for MoO<sub>3</sub> is lower than that of CdS favoring electron injection from photoexcited CdS to MoO<sub>3</sub> as shown in Fig. 1.

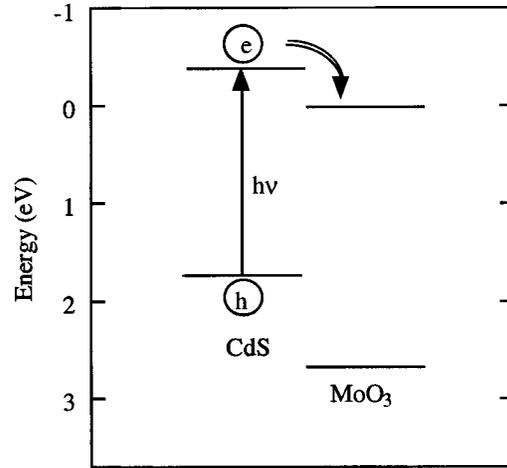


FIG. 1. Energy diagram for the CdS/MoO<sub>3</sub> double-layer system.